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HEWLETT-PACKARD COMPANY			SCHILLINGER, LAURA M		
Intellectual Property Administration P.O. Box 272400			ART UNIT	PAPER NUMBER	
Fort Collins, C	7 -		2813		

DATE MAILED: 02/25/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

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Application No.	Applicant(s)	UN.
09/891,324	NAKAGAWA, OSAMI	J SAMUEL
Examin r	Art Unit	
Laura M Schillinger	2813	
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DETAILED ACTION

This Office Action is in response to Amendment A, dated 5/27/03, in Paper No. 7.

Specification

The specification is objected to as failing to provide proper antecedent basis for the claimed subject matter. See 37 CFR 1.75(d)(1) and MPEP § 608.01(o). Correction of the following is required: Amended claim 1 recites "forming a first electrode in a first <u>dielectric</u> layer", this language contradicts the description provided by Applicant's specification on page 3, lines 17-18, again on page 5, lines: 16-17 which recites "forming a first electrode in a first <u>metal</u> layer".

Note: Despite the contradiction of language found within the specification, amended claim 1 does not add new matter since Fig.s 3A through 3E show the formation of a first electrode (320-324) in a first dielectric layer (305).

Second, amended claim 1 recites "forming a second electrode in a second <u>dielectric</u> layer" this contradicts the description provided by Applicant's specification on page 5, lines: 18-19, which recites "an upper electrode formed in a second <u>metal</u> layer". Again, despite the contradiction of language, amended claim 1 does not constitute new matter since Fig.3E shows the second electrode (350) formed in second dielectric (335).

Applicant should amend the specification so that it does not contradict the Figures and claimed subject matter.

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Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1-4 and 7-12 rejected under 35 U.S.C. 102(b) as being anticipated by Lou ('680).

In reference to claim 1, Lou teaches a method comprising:

Forming a first electrode (Fig.4 (126) and Col. in a first dielectric layer (251) of the multi-level metallization device (100) (Fig.4 and Col. 7, lines: 40-50)

Depositing a substantially thin dielectric material layer (253) over the first dielectric layer (251) of the multi-level metallization device (herein after referred to as "MLM") (100) (Fig.4 and Col. 7, lines: 40-50); and

Forming a second electrode (326) in a second dielectric layer (470), wherein the second dielectric layer (470) is formed substantially over the substantially thin dielectric layer (253) (Fig.4).

In reference to claim 2, Lou teaches further comprising:

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Patterning the substantially thin dielectric material to substantially cover the first electrode (Col.6, lines: 15-16- teaching to pattern layer 250 which is a composite layer including layer 253); and

Adjusting the thickness of the thin dielectric material layer (Col.6, lines: 5-25).

In reference to claim 3, Lou teaches wherein a dielectric constant of the substantially thin dielectric layer is substantially high (Col.5, lines: 5-10- teaching that layer 251 may be silicon nitride which has a substantially high dielectric constant; see also Col.5, lines: 65-67- teaching substantially thin dielectric layer 253 may be made of the same material as 251 (aka silicon nitride)).

In reference to claim 4, Lou teaches wherein the substantially thin dielectric layer includes SiN (Col.5, lines: 5-10- teaching that layer 251 may be silicon nitride; see also Col.5, lines: 65-67-teaching substantially thin dielectric layer 253 may be made of the same material as 251 (aka silicon nitride)).

In reference to claim 7, Lou teaches further comprising:

Depositing a second dielectric layer over the substantially thin dielectric layer (col.4, lines: 10-25); and

Etching at least one via adaptive to receive the second electrode (Col.4, lines: 40-55).

In reference to claim 8, Lou teaches further comprising:

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Polishing the second metal layer (Fig. 6 (38)).

In reference to claim 9, Lou teaches wherein etching the first electrode in a first dielectric layer of the MLM (Col.4, lines: 50-58).

In reference to claim 10, Lou teaches wherein the first electrode is formed in a parallel line configuration (Fig. 5 (30a)).

In reference to claim 11, Lou teaches wherein the second electrode is formed in a parallel line configuration (Fig.6 (38)).

In reference to claim 12, Lou teaches wherein the dielectric is a composite (Col.6, lines: 15-16).

In reference to claim 13, Lou teaches wherein the composite comprises PZT and platinum (Col.6, lines: 5-25).

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

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Claims 5 and 6 are rejected under 35 U.S.C. 103(a) as being unpatentable over Lou ('680).

In reference to claim 5, Lou fails to explicitly teach wherein the thickness of the dielectric layer is between 50 to 100 A- however does teach that the dielectric is thin (Col.6, lines; 5-25). This claim is prima facie obvious without showing that the claimed ranges achieve unexpected results relative to the prior art range. In re Woodruff, 16 USPQ2d 1935, 1937 (Fed. Cir. 1990). See also In re Huang, 40 USPQ2d 1685, 1688(Fed. Cir. 1996)(claimed ranges of a result effective variable, which do not overlap the prior art ranges, are unpatentable unless they produce a new and unexpected result which is different in kind and not merely in degree from the results of the prior art). See also In re Boesch, 205 USPQ 215 (CCPA 1985) (discovery of optimum value of result effective variable in known process is ordinarily within skill of art) and In re Aller, 105 USPQ 233 (CCPA 1955) (selection of optimum ranges within prior art general conditions is obvious).

In reference to claim 6, Lou fails to explicitly teach wherein the dielectric constant is between 4 and 100, however does teach that the dielectric constant for BST is high. This claim is prima facie obvious without showing that the claimed ranges achieve unexpected results relative to the prior art range. In re Woodruff, 16 USPQ2d 1935, 1937 (Fed. Cir. 1990). See also In re Huang, 40 USPQ2d 1685, 1688(Fed. Cir. 1996)(claimed ranges of a result effective variable, which do not overlap the prior art ranges, are unpatentable unless they produce a new and unexpected result which is different in kind and not merely in degree from the results of the prior art). See

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also In re Boesch, 205 USPQ 215 (CCPA 1985) (discovery of optimum value of result effective

variable in known process is ordinarily within skill of art) and In re Aller, 105 USPQ 233 (CCPA

1955) (selection of optimum ranges within prior art general conditions is obvious).

Conclusion

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Laura M Schillinger whose telephone number is (703) 308-6425.

The examiner can normally be reached on M-T, R-F 7:00-5:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Carl W Whitehead, Jr. can be reached on (703) 308-4940. The fax phone number for

the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent

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LMS

February 23, 2004

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